## **SQ4182EY**

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**Vishay Siliconix** 

## Automotive N-Channel 30 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V <sub>DS</sub> (V)	30		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 10 V	0.0038		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = 4.5 V	0.0050		
I <sub>D</sub> (A)	32		
Configuration	Single		

### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 %  $R_q$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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N-Channel MOSFET



COMPLIANT HALOGEN

ORDERING INFORMATION	
Package	SO-8
Lead (Pb)-free and halogen-free	SQ4182EY (for detailed order number please see www.vishav.com/doc?79771)

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	30	V	
Gate-source voltage		V <sub>GS</sub>	± 20	v	
Continuous drain current	$T_C = 25 \ ^{\circ}C \ ^{a}$	- I <sub>D</sub> -	32		
	T <sub>C</sub> = 125 °C		18		
Continuous source current (diode conduction)		IS	6.4	A	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	100		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	60		
Single pulse avalanche energy	L = 0.1 mm	E <sub>AS</sub>	180	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C		7.1	W	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	2.3		
Operating junction and storage temperature range	ge	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	80	°C/W	
Junction-to-foot (drain)		R <sub>thJF</sub>	21	0/11	

#### Notes

a. Package limited

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

c. When mounted on 1" square PCB (FR4 material)

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<b>SPECIFICATIONS</b> ( $T_C = 25 \ ^{\circ}C$	, unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> :	$V_{GS} = 0 V, I_D = 250 \ \mu A$		-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$		2.0	2.5	v
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	20	-	-	Α
		$V_{GS} = 10 V$	I <sub>D</sub> = 14 A	-	0.0031	0.0038	
		$V_{GS} = 10 V$	I <sub>D</sub> = 14 A, T <sub>J</sub> = 125 °C	-	-	0.0060	Ω
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 14 A, T <sub>J</sub> = 175 °C	-	-	0.0070	
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 10 A	-	0.0040	0.0050	
Forward transconductance b	g <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 14 A	-	107	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 15 V, f = 1 MHz	-	4313	5400	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	868	1090	
Reverse transfer capacitance	C <sub>rss</sub>			-	305	390	
Total gate charge <sup>c</sup>	Qg		V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	-	72	110	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		-	14	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	8	-	1
Gate resistance	Rg		f = 1 MHz		1.8	4.9	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	16	24	
Rise time <sup>c</sup>	tr		$V_{DD} = 15 \text{ V}, \text{ R}_{\text{I}} = 1.5 \Omega$		10	15	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	57	86	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	8	12	1
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	100	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		0.75	1.2	V

#### Notes

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2



10

125 °C

15

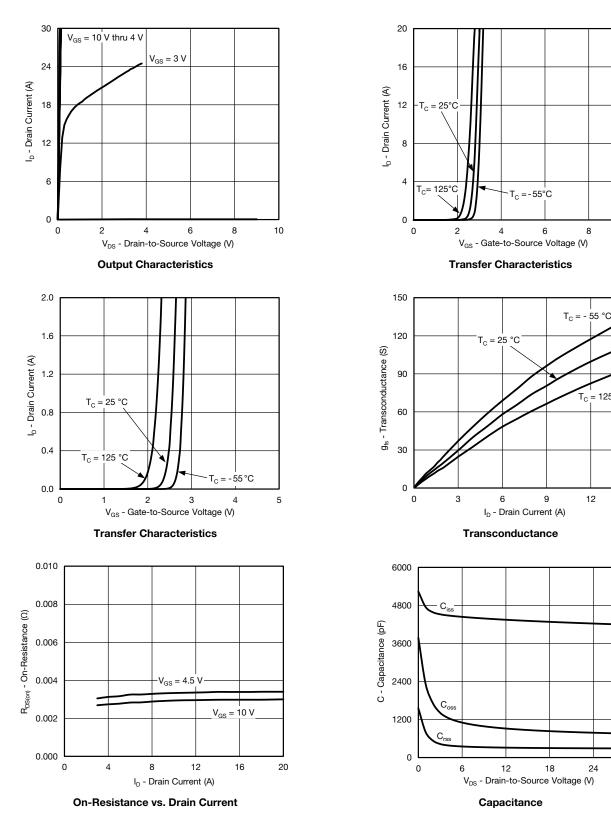
T<sub>C</sub>

12

8

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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



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24

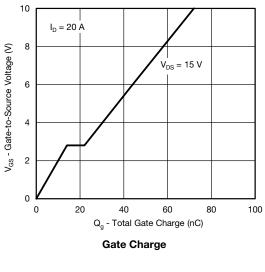
30

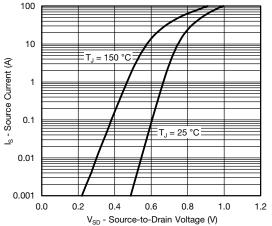
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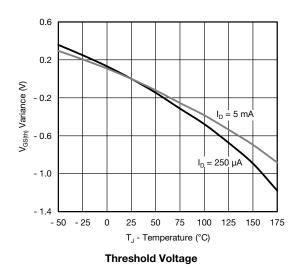
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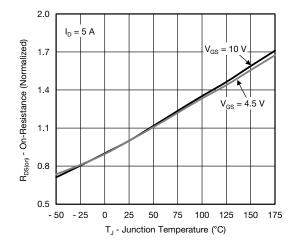
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



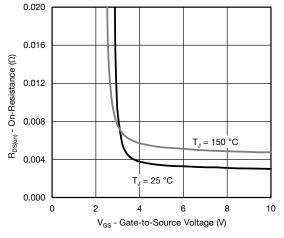


Source Drain Diode Forward Voltage

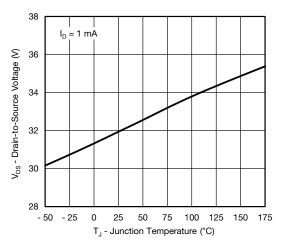




**On-Resistance vs. Junction Temperature** 







Drain Source Breakdown vs. Junction Temperature

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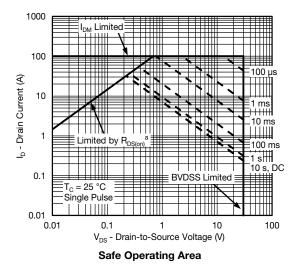
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## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



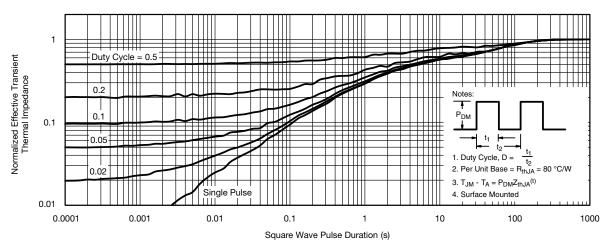
#### Note

a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(\text{on})}$  is specified

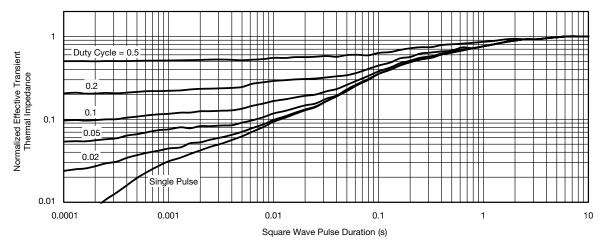


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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# Package Information

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### SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012





	MILLIMETERS		INC	HES	
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					

# **Application Note 826**

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**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)

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